

### ● General Description

The AGM425M combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

This device is ideal for load switch and battery protection applications.

### ● Features

- Advance high cell density Trench technology
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

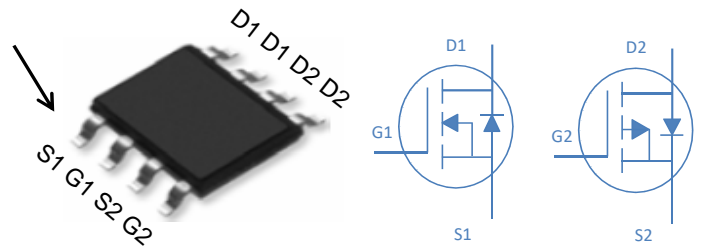
### ● Application

- MB/VGA Vcore
- SMPS 2<sup>nd</sup> Synchronous Rectifier
- POL application
- BLDC Motor driver

### Product Summary

BVDSS	RDSON	ID
40V	25mΩ	6.6A
-40V	65mΩ	-5.5A

### SOP8 Pin Configuration



### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM425M	AGM425M	SOP8	--mm	--mm	3000

**Table 1. Absolute Maximum Ratings (TA=25°C)**

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
$V_{DS}$	Drain-Source Voltage ( $V_{GS}=0V$ )	40	-40	V
$V_{GS}$	Gate-Source Voltage ( $V_{DS}=0V$ )	±20	±20	V
$I_D$	Drain Current-Continuous( $T_c=25^\circ C$ ) <b>(Note 1)</b>	6.6	-5.5	A
	Drain Current-Continuous( $T_c=100^\circ C$ )	4.3	-3.7	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed <b>(Note 2)</b>	17	-15	A
$P_D$	Total Power Dissipation( $T_c=25^\circ C$ )	1.3	2.0	W
	Total Power Dissipation( $T_c=100^\circ C$ )	0.7	0.7	W
EAS	Avalanche energy <b>(Note 3)</b>	22	18	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	-55 To 150	°C

**Table 2. Thermal Characteristic**

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	---	62.5	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	--	°C/W

**Table 3. N- Channel Electrical Characteristics (TA=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>On/Off States</b>						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	40	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=40V, VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	1.1	1.5	2.5	V
gFS	Forward Transconductance	VDS=5V, ID=6A	--	--	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=5A	--	25	37	mΩ
		VGS=4.5V, ID=3A	--	41	60	mΩ
<b>Dynamic Characteristics</b>						
Ciss	Input Capacitance	VDS=20V, VGS=0V, F=1MHZ	--	495	--	pF
Coss	Output Capacitance		--	42	--	pF
Crss	Reverse Transfer Capacitance		--	33	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V, f=1.0MHz	--	--	--	Ω
<b>Switching Times</b>						
td(on)	Turn-on Delay Time	VGS=10V, VDS=20V, ID=3.5A, RGEN=3Ω	--	15	--	nS
tr	Turn-on Rise Time		--	49.5	--	nS
td(off)	Turn-Off Delay Time		--	19.2	--	nS
tf	Turn-Off Fall Time		--	11	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=20V, ID=3.5A	--	10	--	nC
Qgs	Gate-Source Charge		--	1.4	--	nC
Qgd	Gate-Drain Charge		--	1.9	--	nC
<b>Source-Drain Diode Characteristics</b>						
ISD	Source-Drain Current(Body Diode)		--	--	6.6	A
VSD	Forward on Voltage	VGS=0V, IS=1A	--	--	1.2	V
trr	Reverse Recovery Time	IF=1A , di/dt=100A/μs ,	--	--	--	ns
Qrr	Reverse Recovery Charge	TJ=25°C	--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C

**Table 3. P-Channel Electrical Characteristics (TA=25°C unless otherwise noted)**

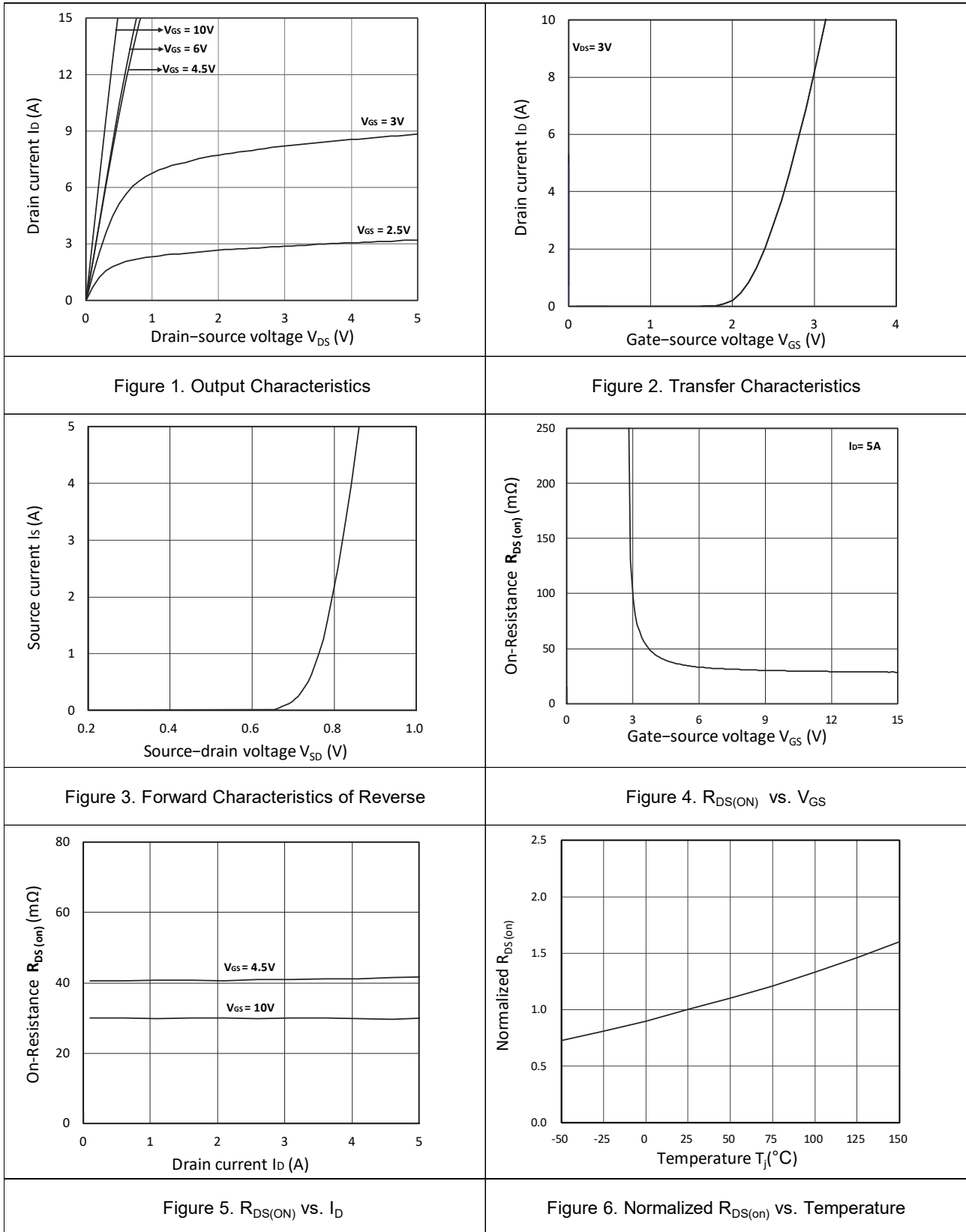
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>On/Off States</b>						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=-250μA	-40	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-40V, VGS=0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=-250μA	-1.2	-1.9	-2.5	V
gFS	Forward Transconductance	VDS=-15V, ID=-3.1A	10	--	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-5A	--	65	80	mΩ
		VGS=-4.5V, ID=-4A	--	92	120	mΩ
<b>Dynamic Characteristics</b>						
Ciss	Input Capacitance	VDS=-20V, VGS=0V, F=1MHZ	--	600	--	pF
Coss	Output Capacitance		--	90	--	pF
Crss	Reverse Transfer Capacitance		--	70	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V, f=1.0MHz	--	--	--	Ω
<b>Switching Times</b>						
td(on)	Turn-on Delay Time	VGS=-10V, VDS=-20V, RL=2Ω, RGEN=3Ω	--	9	--	nS
tr	Turn-on Rise Time		--	8	--	nS
td(off)	Turn-Off Delay Time		--	28	--	nS
tf	Turn-Off Fall Time		--	10	--	nS
Qg	Total Gate Charge	VGS=-10V, VDS=-20V, ID=-5A	--	14	--	nC
Qgs	Gate-Source Charge		--	2.9	--	nC
Qgd	Gate-Drain Charge		--	3.8	--	nC
<b>Source-Drain Diode Characteristics</b>						
ISD	Source-Drain Current(Body Diode)		--	--	-5.5	A
VSD	Forward on Voltage	VGS=0V, IS=-5A	--	--	-1.2	V
trr	Reverse Recovery Time	IF=-5A , di/dt=100A/μs ,	--	--	--	ns
Qrr	Reverse Recovery Charge	TJ=25°C	--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature Notes

3.EAS condition: TJ=25°C

## Typical Characteristics



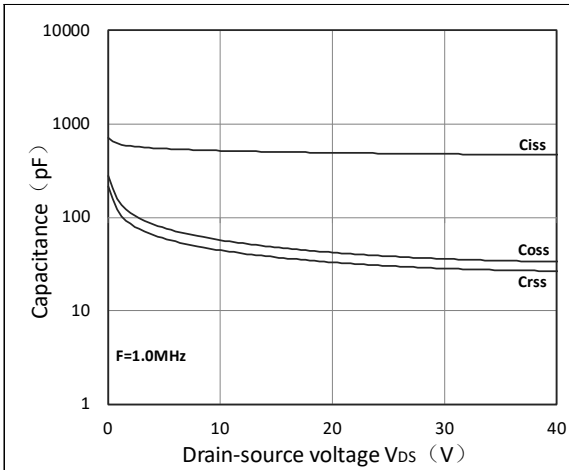


Figure 7. Capacitance Characteristics

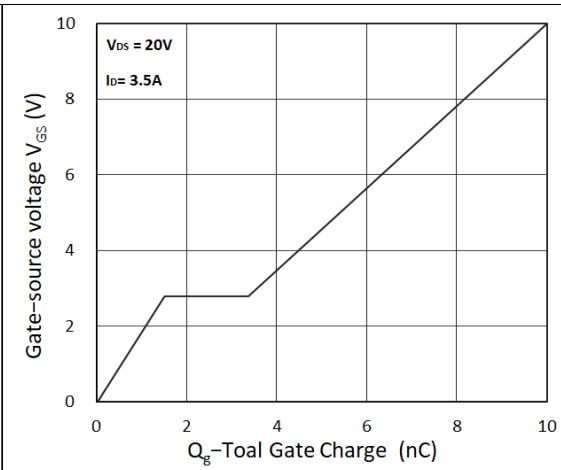


Figure 8. Gate Charge Characteristics

### Typical Electrical and Thermal Characteristics

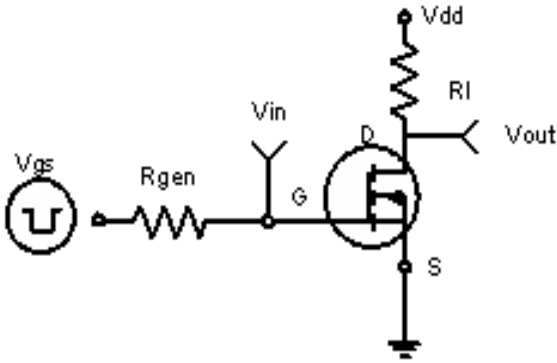


Figure 1: Switching Test Circuit

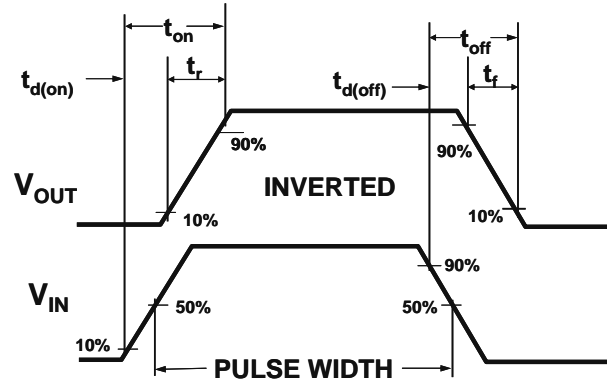


Figure 2: Switching Waveforms

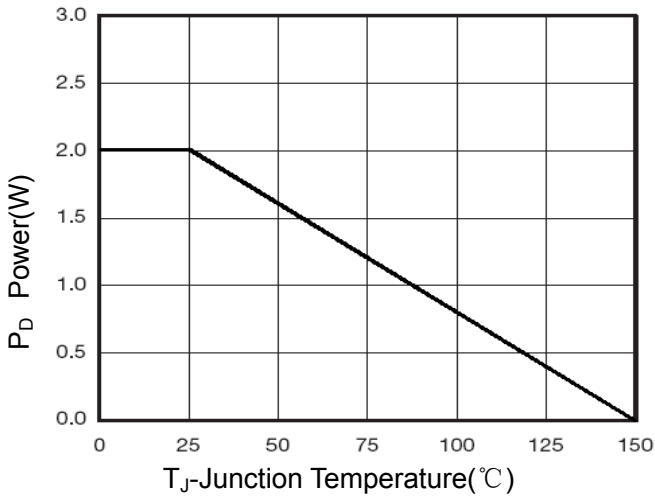


Figure 3 Power Dissipation

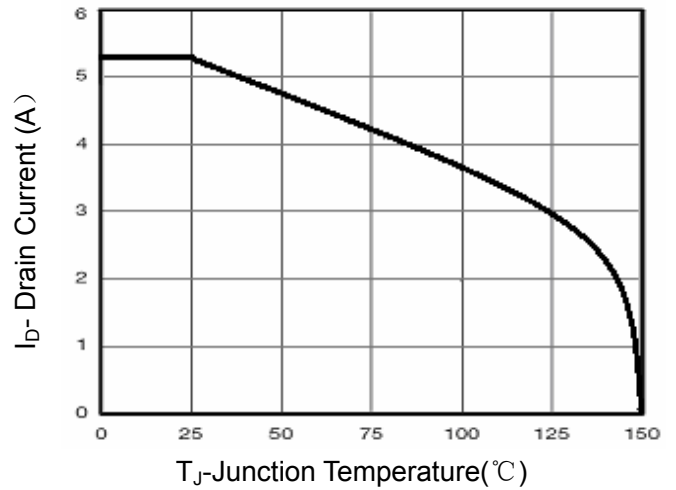


Figure 4 Drain Current

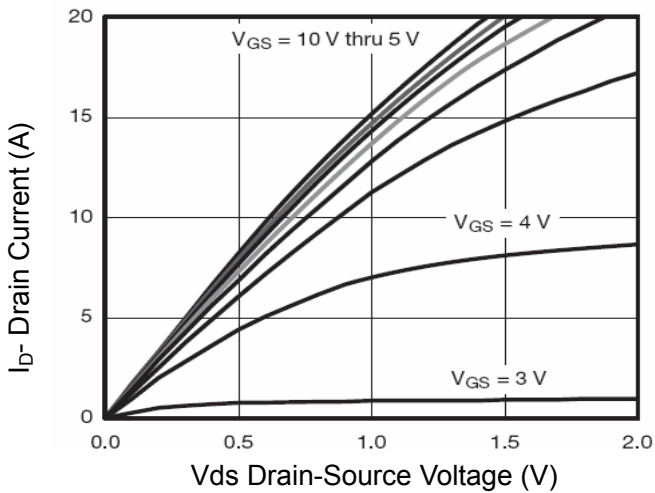


Figure 5 Output Characteristics

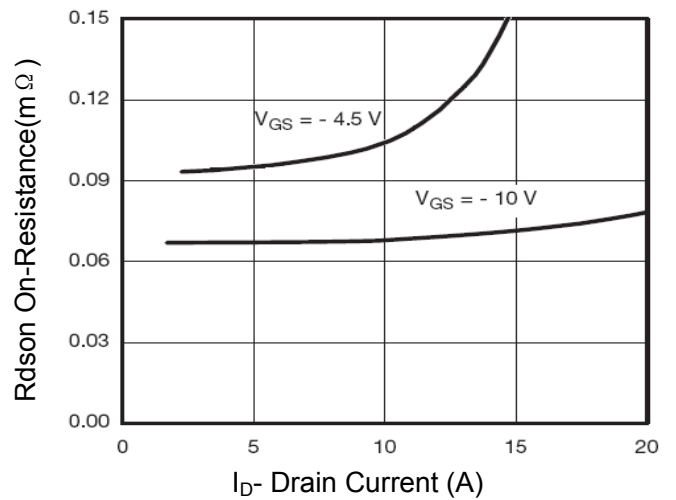
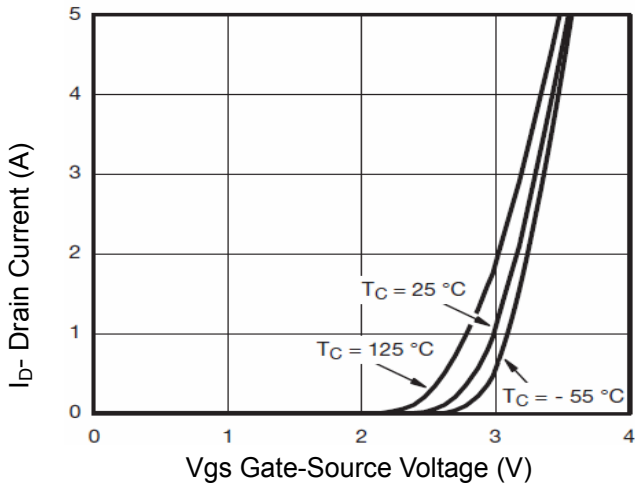
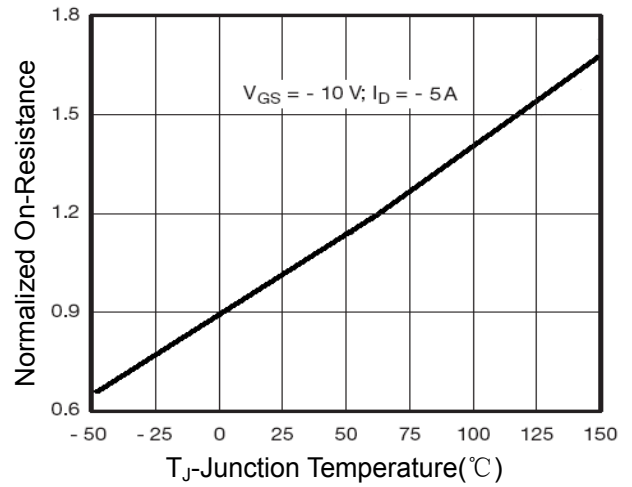
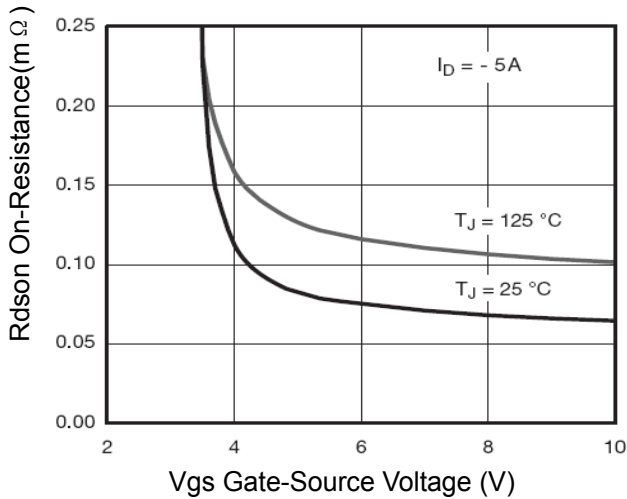
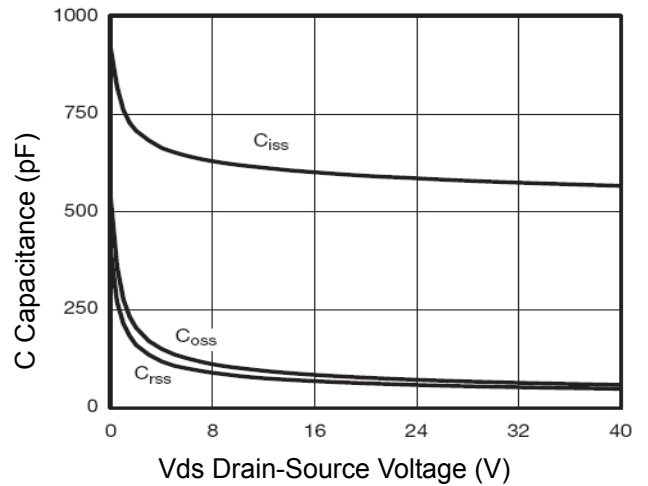
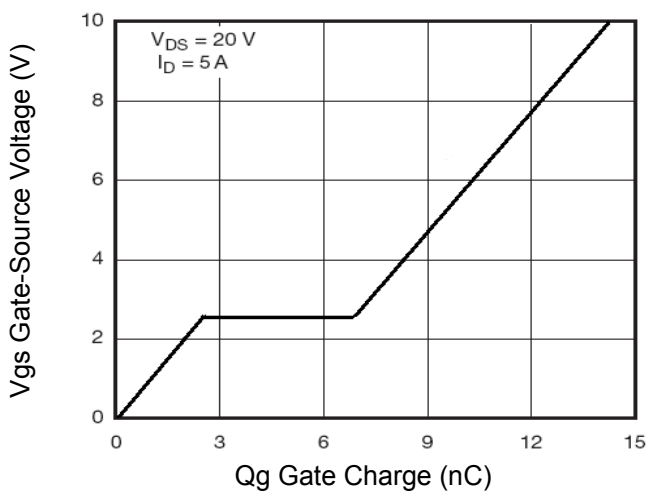
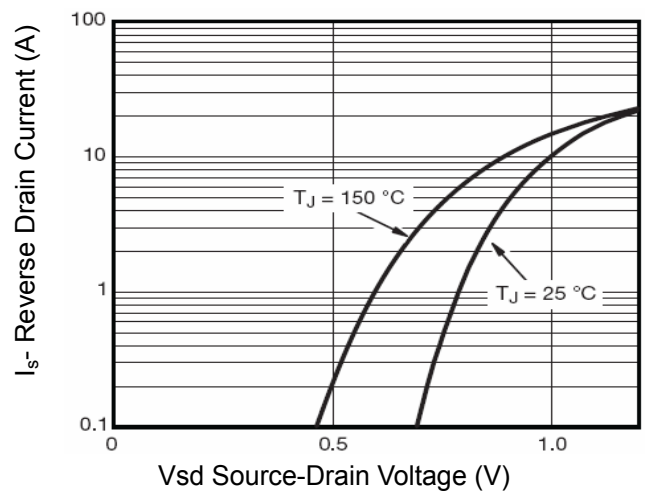
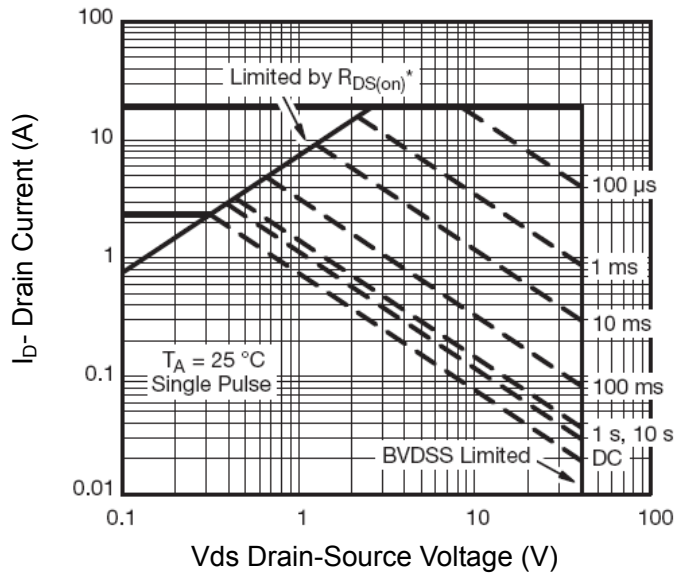
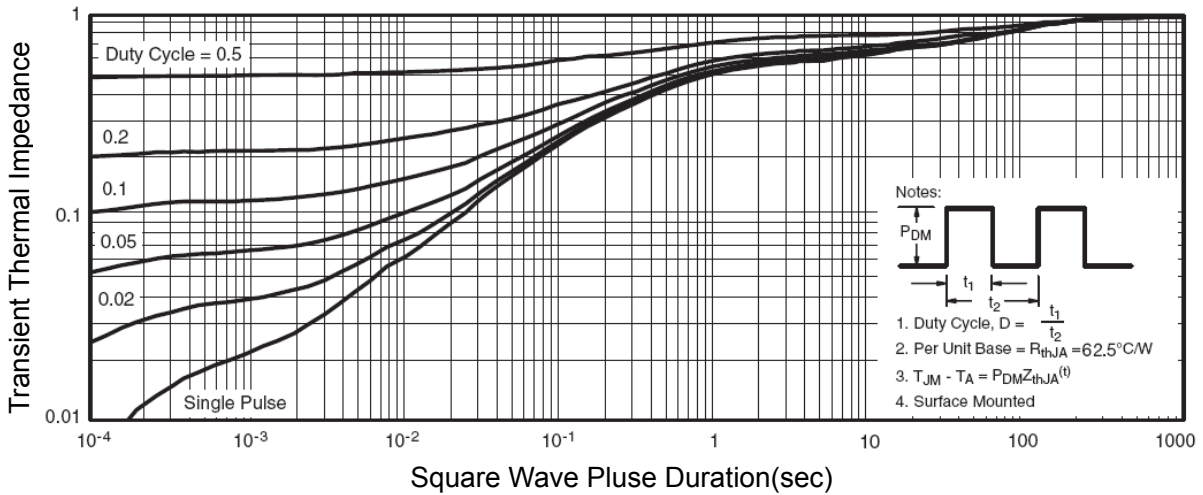


Figure 6 Drain-Source On-Resistance


**Figure 7 Transfer Characteristics**

**Figure 8 Drain-Source On-Resistance**

**Figure 9 Rdson vs Vgs**

**Figure 10 Capacitance vs Vds**

**Figure 11 Gate Charge**

**Figure 12 Source- Drain Diode Forward**



**Figure 13 Safe Operation Area**

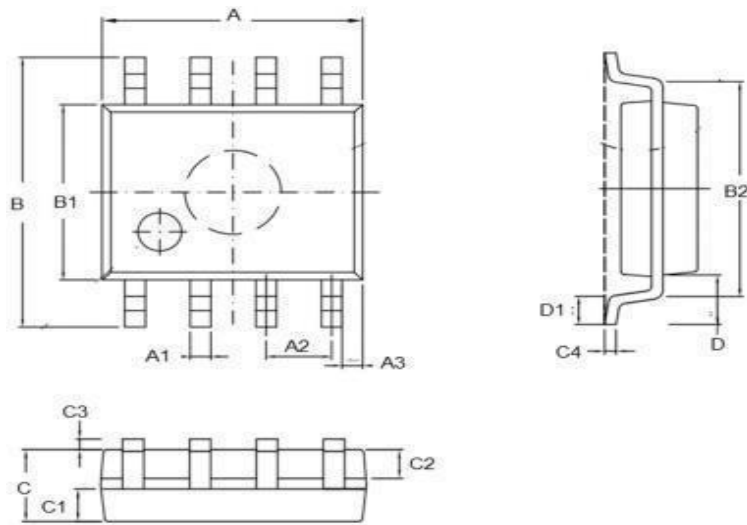


**Figure 14 Normalized Maximum Transient Thermal Impedance**



**•Dimensions(SOP8)**

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.00	C	1.30		1.50
A1	0.37		0.47	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.19	0.20	0.23
B1	3.80		4.00	D		1.05	
B2		5.00		D1	0.40		0.62




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